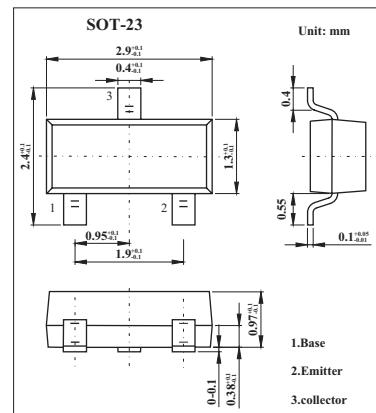


NPN General Purpose Transistor

2PD601A

■ Features

- Low current (max. 100 mA)
- Low voltage (max. 50 V).



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	60	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EBO}	6	V
Collector current (DC)	I _C	100	mA
Peak collector current	I _{CM}	200	mA
Peak base current	I _{BM}	100	mA
Total power dissipation Tamb≤25°C; *	P _{tot}	250	mW
Storage temperature	T _{stg}	-65 to +150	°C
Junction temperature	T _j	150	°C
Operating ambient temperature	T _{amb}	-65 to +150	°C
Thermal resistance from junction to ambient *	R _{th j-a}	500	K/W

* Transistor mounted on an FR4 printed-circuit board.

2PD601A■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cut-off current	I_{CBO}	$I_E = 0; V_{CB} = 60 \text{ V}$			10	nA
		$I_E = 0; V_{CB} = 60 \text{ V}; T_j = 150^\circ\text{C}$			5	μA
Emitter cut-off current	I_{EBO}	$I_C = 0; V_{EB} = 5 \text{ V}$			10	nA
DC current gain 2PD601AQ 2PD601AR 2PD601AS	h_{FE}	$I_C = 2 \text{ mA}; V_{CE} = 10 \text{ V}; *$	160		260	
			210		340	
			290		460	
DC current gain	h_{FE}	$I_C = 100 \text{ mA}; V_{CE} = 2 \text{ V};$	90			
Collector-emitter saturation voltage	V_{CESat}	$I_C = 100 \text{ mA}; I_B = 10 \text{ mA}; *$			500	mV
Collector capacitance	C_C	$I_E = i_E = 0; V_{CB} = 10 \text{ V}; f = 1 \text{ MHz}$			3.5	pF
Transition frequency 2PD601AQ 2PD601AR 2PD601AS	f_T	$I_C = 2 \text{ mA}; V_{CE} = 10 \text{ V}; f = 100 \text{ MHz} *$	100			MHz
			120			
			140			

* Pulse test: $tp \leq 300 \mu\text{s}$; $\delta \leq 0.02$.

■ Marking

Type Number	2PD601AQ	2PD601AR	2PD601AS
Marking	ZQ	ZR	ZS